

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number ~~Unknown~~ 10/727,765

Filing Date 12/3/03 ✓

First Named Inventor Herner, S. Brad

Group Art Unit ~~Unknown~~ 2815Examiner Name ~~Unknown~~ Jay C. Kim

Sheet 1 of 1

Attorney Docket No: MA-070-1

**US PATENT DOCUMENTS**

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
J. K.	A1	10/185507		Vyvoda et al.			06/27/2002
J. K.	A2	10/326470		Herner et al.			12/19/2002
J. K.	A3	10/440882		Vyvoda			05/19/2003
J. K.	A4	10/610804		Herner et al.			06/30/2003
J. K.	A5	10/611245		Herner			06/30/2003
J. K.	A6	6034882	03/07/2000	Johnson et al.			
J. K.	A7	6420215	07/16/2002	Knall et al.			
J. K.	A8	6525953	02/25/2003	Johnson			
J. K.	A9	6541312	04/01/2003	Vyvoda et al.			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
---------------------	---------	---------------------	------------------	---	-------	----------	----------------

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
J. K.	A10	CHIANG, STEVE., et al. , "Antifuse Structure Comparison for Field Programmable Gate Arrays", IEDM 92-611, (4/1992), 24.6.1-24.6.4	
J. K.	A11	HAMDY, ESMAT., et al. , "Dielectric Based Antifuse for Logic and Memory ICs", IEDM 88, (1988), 786-789	
J. K.	A12	HERNER, S..B. , et al. , "Polycrystalline silicon/CoSi <sub>2</sub> Schottky diode with integrated SiO <sub>2</sub> antifuse: a nonvolatile memory cell", Applied Physics Letters, Volume 82, Number 23, 9 June 2003, (6/9/2003), 4163-4165	
J. K.	A13	KONAKOVA, R..V. , et al. , "Ohmic Contacts for Microwave Diodes", Proc. 22nd International Conference on Microelectronics (MIEL 2000), VOL 2, NIS, Serbia, 14-17 May 2000, (1/1999), 477-480	
J. K.	A14	SHIH, CHIH-CHING., et al. , "Characterization and Modeling of a Highly Reliable Metal-to-Metal Antifuse for High-Performance and High-Density Field-Programmable Gate Arrays", 1997 IEEE, (9/1997), 25-33	
J. K.	A15	WANG, SHOU-JEN., et al. , "High-Performance Metal/Silicide Antifuse", IEEE Electron Device Letters, VOL.13, NO 9, September 1992, (9/1992), 471-472	

EXAMINER

DATE CONSIDERED

5/30/07

Substitute Disclosure Statement Form (PTO-1448)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional) <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached